Small Signal MOSFET

20 V, Dual N-Channel, SC-88 ESD Protection

Features

- Small Footprint (2 x 2 mm)
- Low Gate Charge N-Channel Device
- ESD Protected Gate
- Same Package as SC-70 (6 Leads)
- AEC-Q101 Qualified and PPAP Capable NVJD4401N
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Load Power Switching
- Li-Ion Battery Supplied Devices
- Cell Phones, Media Players, Digital Cameras, PDAs
- DC-DC Conversion

MAXIMUM RATINGS (T_{.I} = 25°C unless otherwise stated)

Param	Symbol	Value	Unit			
Drain-to-Source Voltage	V_{DSS}	20	V			
Gate-to-Source Voltage	,		V_{GS}	±12	V	
Continuous Drain Current	Steady State	T _A = 25°C	I _D	0.63	Α	
(Based on $R_{\theta JA}$)	State	T _A = 85°C		0.46		
Power Dissipation	Steady State	T _A = 25°C	P _D	0.27	W	
(Based on R _{θJA})	State	T _A = 85°C		0.14		
Continuous Drain Current	Steady State	T _A = 25°C	I _D	0.91	Α	
(Based on R _{θJL})	State	T _A = 85°C		0.65		
Power Dissipation	Steady	T _A = 25°C	_	0.55	W	
(Based on R _{θJL})	State	T _A = 85°C	P _D	0.29		
Pulsed Drain Current	I _{DM}	±1.2	Α			
Operating Junction and	T_J, T_{STG}	–55 to 150	°C			
Continuous Source Curr	I _S	0.63	Α			
Lead Temperature for So (1/8" from case for 10 s)	T _L	260	°C			

THERMAL RESISTANCE RATINGS (Note 1)

Parameter	Symbol	Тур	Max	Units
Junction-to-Ambient - Steady State	$R_{\theta JA}$	400	458	°C/W
Junction-to-Lead (Drain) - Steady State	$R_{ heta JL}$	194	252	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface mounted on FR4 board using 1 oz Cu area = 0.9523 in sq.

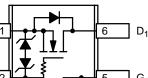


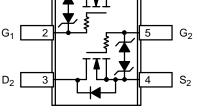
ON Semiconductor®

www.onsemi.com

V _{(BR)DSS}	R _{DS(on)} Typ	I _D Max
20 V	0.29 Ω @ 4.5 V	0.63 A
	0.36 Ω @ 2.5 V	0.03 A

SC-88 (SOT-363)

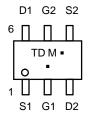




Top View

MARKING DIAGRAM & PIN ASSIGNMENT





TD = Device Code M = Date Code ■ Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise stated)

Parameter	Symbol	Test Cond	dition	Min	Тур	Max	Unit
OFF CHARACTERISTICS							
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		20	27		V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J				22		mV/ °C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _E	_{DS} = 16 V			1.0	μΑ
Gate-to-Source Leakage Current	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{G}$	_{iS} = ±12 V			10	μΑ
ON CHARACTERISTICS (Note 2)							
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}, I_{D}$	= 250 μΑ	0.6	0.92	1.5	V
Gate Threshold Temperature Coefficient	V _{GS(TH)} /T _J				-2.1		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 4.5 V, I _I	_D = 0.63 A		0.29	0.375	Ω
		$V_{GS} = 2.5 \text{ V}, I_D = 0.40 \text{ A}$			0.36	0.445	7
Forward Transconductance	9 _{FS}	$V_{DS} = 4.0 \text{ V}, I_{D} = 0.63 \text{ A}$			2.0		S
CHARGES AND CAPACITANCES					-		
Input Capacitance	C _{ISS}	$V_{GS} = 0 \text{ V, } f = 1.0 \text{ MHz,}$ $V_{DS} = 20 \text{ V}$			33	46	pF
Output Capacitance	C _{OSS}				13	22	-
Reverse Transfer Capacitance	C _{RSS}				2.8	5.0	
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 10 V,			1.3	3.0	nC
Threshold Gate Charge	Q _{G(TH)}				0.1		
Gate-to-Source Charge	Q_{GS}	$I_{D} = 0.6$	3 A		0.2		
Gate-to-Drain Charge	Q_GD				0.4		
SWITCHING CHARACTERISTICS (No	ote 3)						
Turn-On Delay Time	td _(ON)				0.083		μS
Rise Time	tr	V _{GS} = 4.5 V, V	_{DD} = 10 V,		0.227		
Turn-Off Delay Time	td _(OFF)	$I_D = 0.5 \text{ A}, R_G = 20 \Omega$			0.786		
Fall Time	tf				0.506		
DRAIN-SOURCE DIODE CHARACTE	RISTICS						
Forward Diode Voltage	V_{SD}	$V_{GS} = 0 V,$	T _J = 25°C		0.76	1.1	V
		I _S =0.23 A	T _J = 125°C		0.63		
Reverse Recovery Time	t _{RR}	$V_{GS} = 0 \text{ V, dI}_{S}/dt$ $I_{S} = 0.6$	= 100 A/μs, 3 A		0.410		μs

Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
 Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)

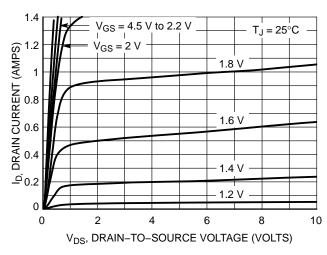


Figure 1. On-Region Characteristics

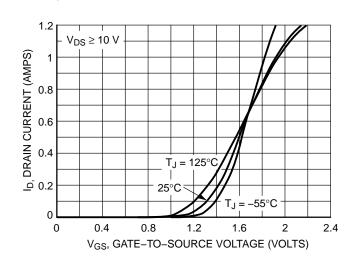


Figure 2. Transfer Characteristics

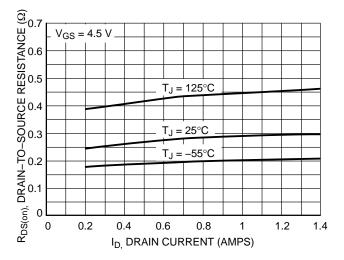


Figure 3. On–Resistance vs. Drain Current and Temperature

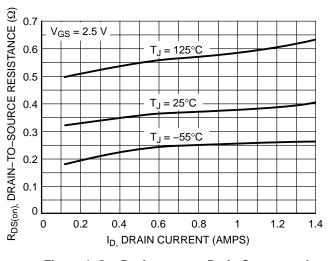


Figure 4. On–Resistance vs. Drain Current and Temperature

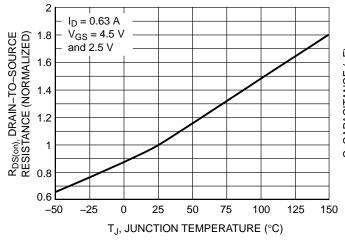


Figure 5. On–Resistance Variation with Temperature

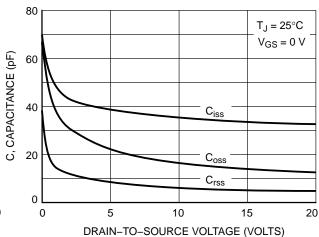


Figure 6. Capacitance Variation

TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)

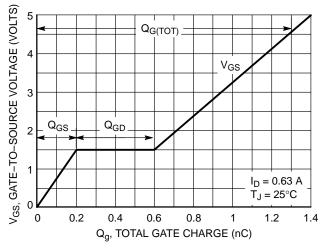


Figure 7. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

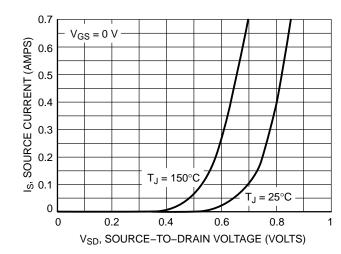


Figure 8. Diode Forward Voltage vs. Current

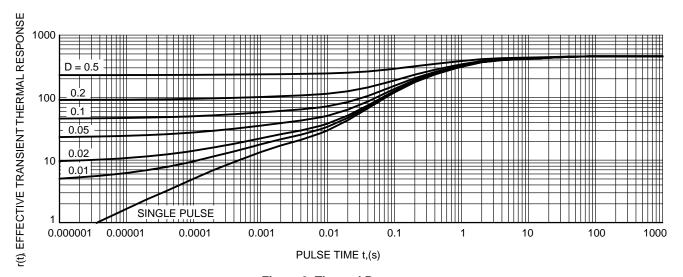


Figure 9. Thermal Response

ORDERING INFORMATION

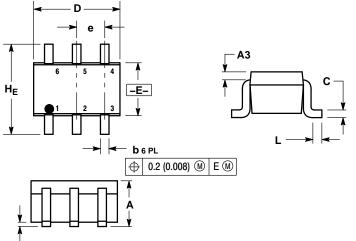
Device	Package	Shipping [†]
NTJD4401NT1G	SC-88 (Pb-Free)	3000 / Tape & Reel
NVJD4401NT1G	SC-88 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363

CASE 419B-02 **ISSUE W**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
- 419B-01 OBSOLETE, NEW STANDARD 419B-02.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.80	0.95	1.10	0.031	0.037	0.043
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3		0.20 RE	F	0.008 REF		
b	0.10	0.21	0.30	0.004	0.008	0.012
С	0.10	0.14	0.25	0.004	0.005	0.010
D	1.80	2.00	2.20	0.070	0.078	0.086
Е	1.15	1.25	1.35	0.045	0.049	0.053
е	0.65 BSC			0	.026 BS	С
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	2.00	2.10	2.20	0.078	0.082	0.086

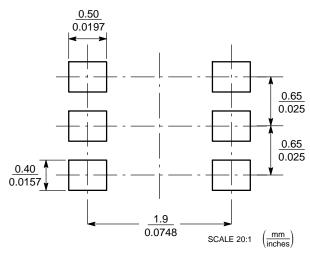
STYLE 26:

- PIN 1. SOURCE 1 2. GATE 1

 - 3. DRAIN 2 4. SOURCE 2

 - 5. GATE 2 6. DRAIN 1

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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